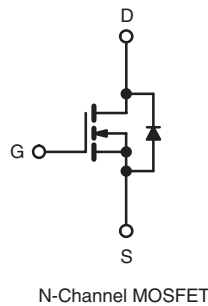
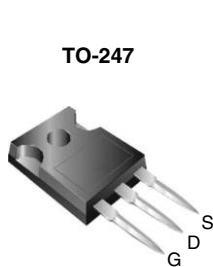


Power MOSFET

| PRODUCT SUMMARY | |
|---------------------------|-------------------------------|
| V_{DS} (V) | 500 |
| $R_{DS(on)}$ (Ω) | $V_{GS} = 10\text{ V}$ 0.27 |
| Q_g (Max.) (nC) | 210 |
| Q_{gs} (nC) | 29 |
| Q_{gd} (nC) | 110 |
| Configuration | Single |



FEATURES

- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- Isolated Central Mounting Hole
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available



DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because its isolated mounting hole. It also provides greater creepage distances between pins to meet the requirements of most safety specifications.

| ORDERING INFORMATION | |
|----------------------|-------------|
| Package | TO-247 |
| Lead (Pb)-free | IRFP460PbF |
| | SiHFP460-E3 |
| SnPb | IRFP460 |
| | SiHFP460 |

| ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | |
|--|----------------------------------|-----------------------------------|---------------------|------------------|
| PARAMETER | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | V_{DS} | 500 | V | |
| Gate-Source Voltage | V_{GS} | ± 20 | | |
| Continuous Drain Current | V_{GS} at 10 V | $T_C = 25\text{ }^\circ\text{C}$ | 20 | A |
| | | $T_C = 100\text{ }^\circ\text{C}$ | 13 | |
| Pulsed Drain Current ^a | I_{DM} | 80 | | |
| Linear Derating Factor | | 2.2 | W/ $^\circ\text{C}$ | |
| Single Pulse Avalanche Energy ^b | E_{AS} | 960 | mJ | |
| Repetitive Avalanche Current ^a | I_{AR} | 20 | A | |
| Repetitive Avalanche Energy ^a | E_{AR} | 28 | mJ | |
| Maximum Power Dissipation | $T_C = 25\text{ }^\circ\text{C}$ | P_D | 280 | W |
| Peak Diode Recovery dV/dt^c | | dV/dt | 3.5 | V/ns |
| Operating Junction and Storage Temperature Range | | T_J, T_{stg} | - 55 to + 150 | $^\circ\text{C}$ |
| Soldering Recommendations (Peak Temperature) | for 10 s | | 300 ^d | |
| Mounting Torque | 6-32 or M3 screw | | 10 | lbf · in |
| | | | 1.1 | N · m |

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 4.3\text{ mH}$, $R_G = 25\text{ }\Omega$, $I_{AS} = 20\text{ A}$ (see fig. 12).
- $I_{SD} \leq 20\text{ A}$, $dI/dt \leq 160\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

| THERMAL RESISTANCE RATINGS | | | | |
|-------------------------------------|------------|------|------|------|
| PARAMETER | SYMBOL | TYP. | MAX. | UNIT |
| Maximum Junction-to-Ambient | R_{thJA} | - | 40 | °C/W |
| Case-to-Sink, Flat, Greased Surface | R_{thCS} | 0.24 | - | |
| Maximum Junction-to-Case (Drain) | R_{thJC} | - | 0.45 | |

| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | | |
|--|---------------------|--|--|------|------|-----------|---------------|
| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
| Static | | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$ | | 500 | - | - | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$ | | - | 0.63 | - | V/°C |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | | 2.0 | - | 4.0 | V |
| Gate-Source Leakage | I_{GSS} | $V_{GS} = \pm 20\text{ V}$ | | - | - | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 500\text{ V}, V_{GS} = 0\text{ V}$ | | - | - | 25 | μA |
| | | $V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$ | | - | - | 250 | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS} = 10\text{ V}$ | $I_D = 12\text{ A}^b$ | - | - | 0.27 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 50\text{ V}, I_D = 12\text{ A}^b$ | | 13 | - | - | S |
| Dynamic | | | | | | | |
| Input Capacitance | C_{iss} | $V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz},$ see fig. 5 | | - | 4200 | - | pF |
| Output Capacitance | C_{oss} | | | - | 870 | - | |
| Reverse Transfer Capacitance | C_{riss} | | | - | 350 | - | |
| Total Gate Charge | Q_g | $V_{GS} = 10\text{ V}$ | $I_D = 20\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 ^b | - | - | 210 | nC |
| Gate-Source Charge | Q_{gs} | | | - | - | 29 | |
| Gate-Drain Charge | Q_{gd} | | | - | - | 110 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 250\text{ V}, I_D = 20\text{ A},$ $R_G = 4.3\text{ }\Omega, R_D = 13\text{ }\Omega,$ see fig. 10 ^b | | - | 18 | - | ns |
| Rise Time | t_r | | | - | 59 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | - | 110 | - | |
| Fall Time | t_f | | | - | 58 | - | |
| Internal Drain Inductance | L_D | Between lead, 6 mm (0.25") from package and center of die contact | | - | 5.0 | - | nH |
| Internal Source Inductance | L_S | | | - | 13 | - | |
| Drain-Source Body Diode Characteristics | | | | | | | |
| Continuous Source-Drain Diode Current | I_S | MOSFET symbol showing the integral reverse p - n junction diode | | - | - | 20 | A |
| Pulsed Diode Forward Current ^a | I_{SM} | | | - | - | 80 | |
| Body Diode Voltage | V_{SD} | $T_J = 25\text{ }^\circ\text{C}, I_S = 20\text{ A}, V_{GS} = 0\text{ V}^b$ | | - | - | 1.8 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $T_J = 25\text{ }^\circ\text{C}, I_F = 20\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$ | | - | 570 | 860 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | - | 5.7 | 8.6 | μC |
| Forward Turn-On Time | t_{on} | Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D) | | | | | |

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

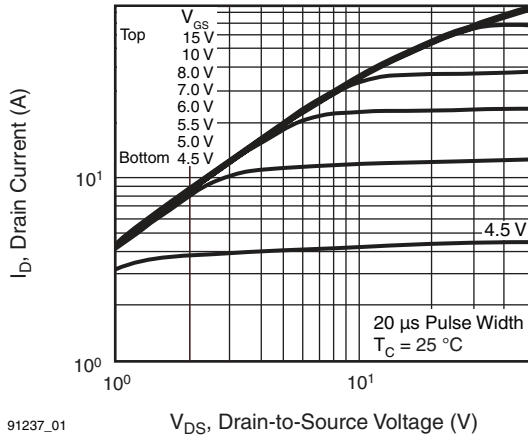


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

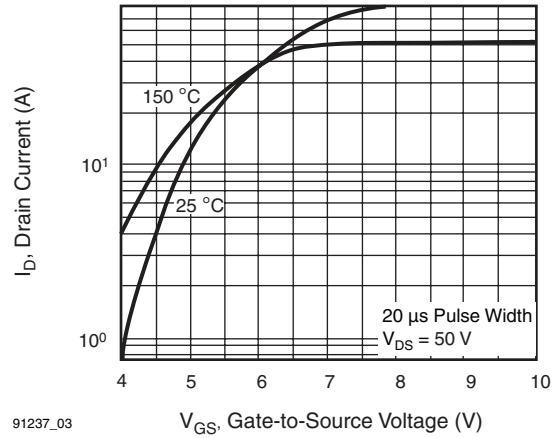


Fig. 3 - Typical Transfer Characteristics

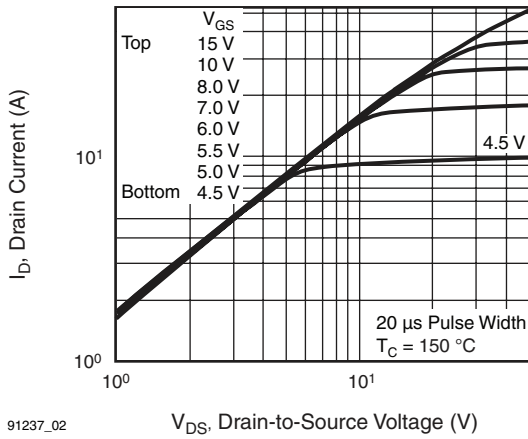


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

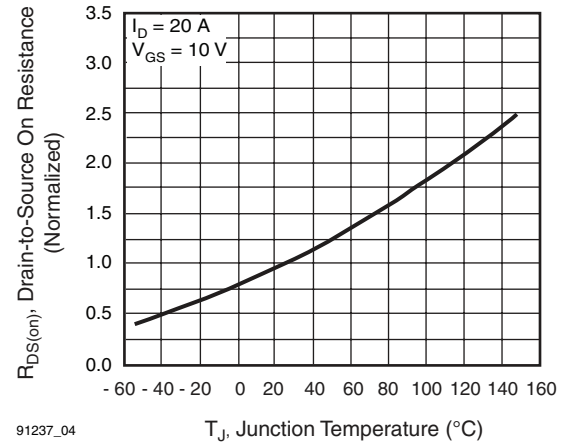
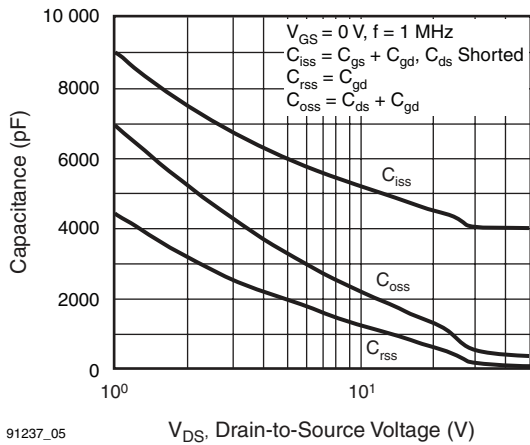
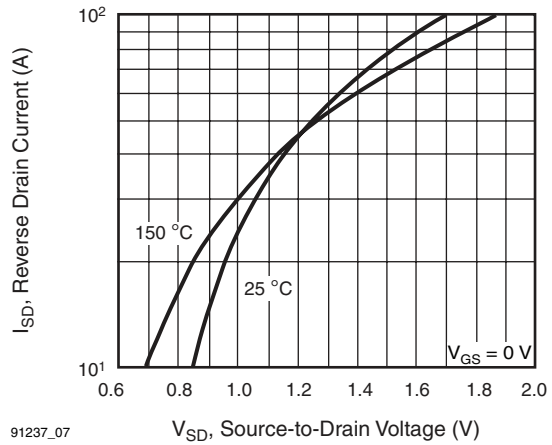


Fig. 4 - Normalized On-Resistance vs. Temperature



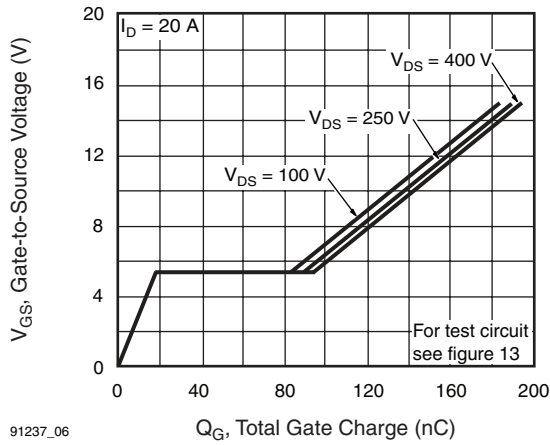
91237_05

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



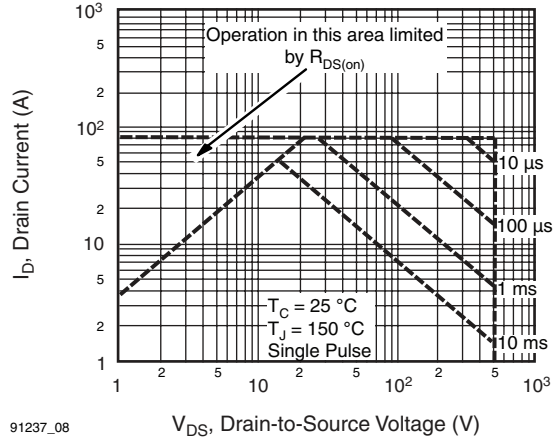
91237_07

Fig. 7 - Typical Source-Drain Diode Forward Voltage



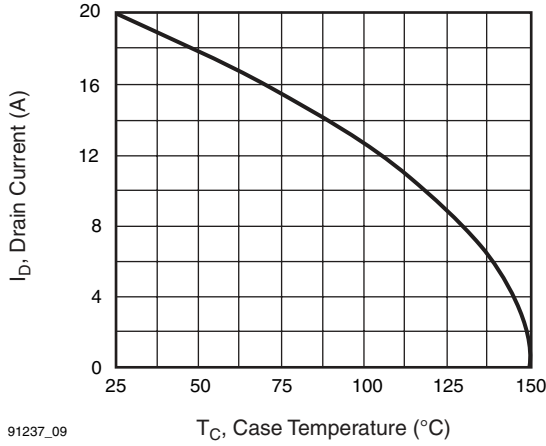
91237_06

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91237_08

Fig. 8 - Maximum Safe Operating Area



91237_09

Fig. 9 - Maximum Drain Current vs. Case Temperature

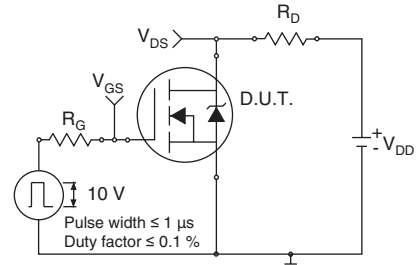


Fig. 10a - Switching Time Test Circuit

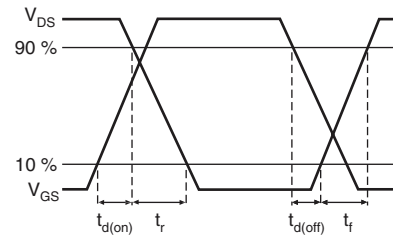
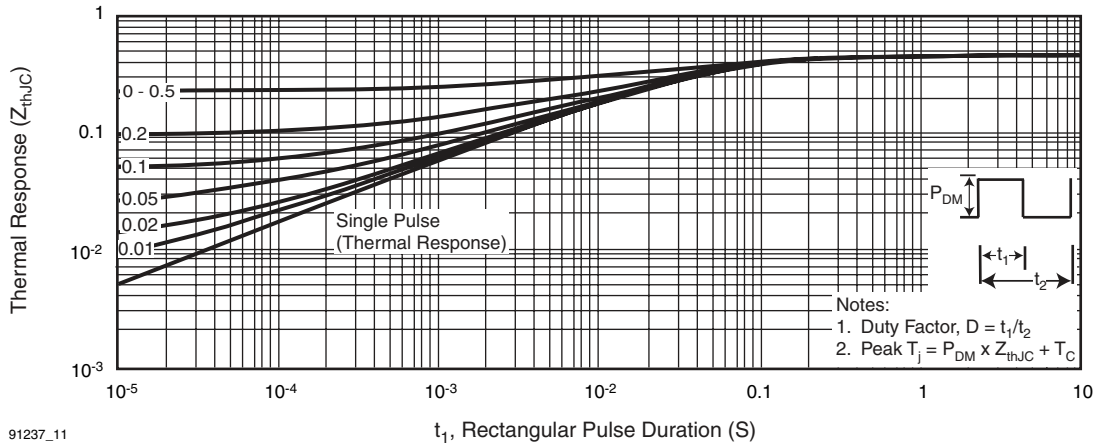


Fig. 10b - Switching Time Waveforms



91237_11

Fig. 11a - Maximum Effective Transient Thermal Impedance, Junction-to-Case

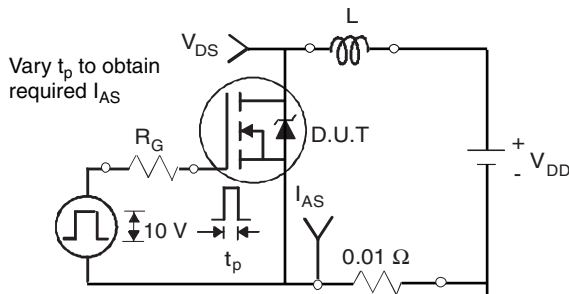


Fig. 12a - Unclamped Inductive Test Circuit

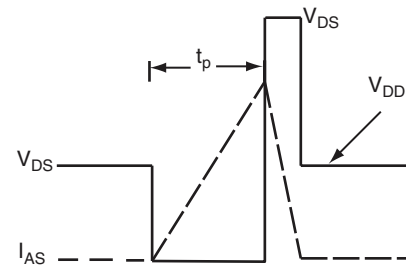


Fig. 12b - Unclamped Inductive Waveforms

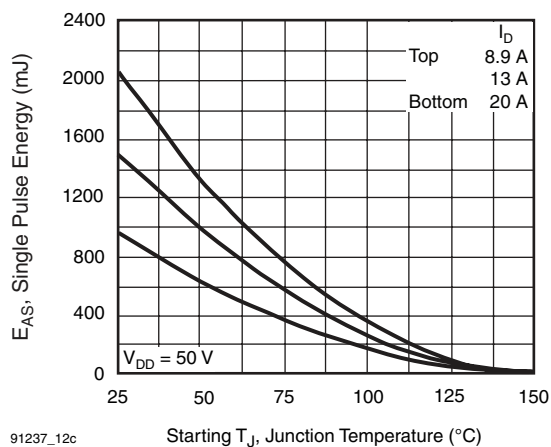


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

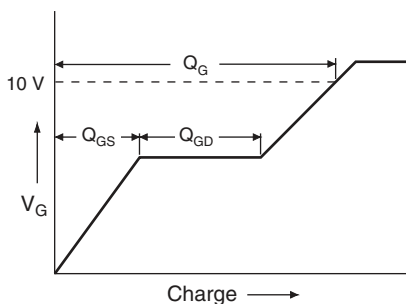


Fig. 13a - Basic Gate Charge Waveform

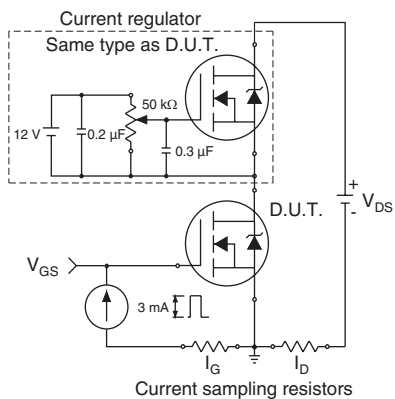


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit

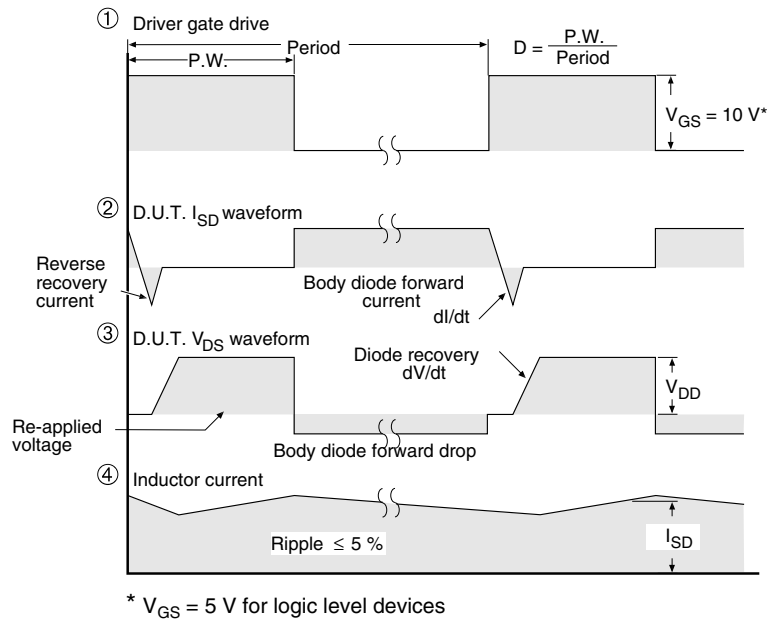
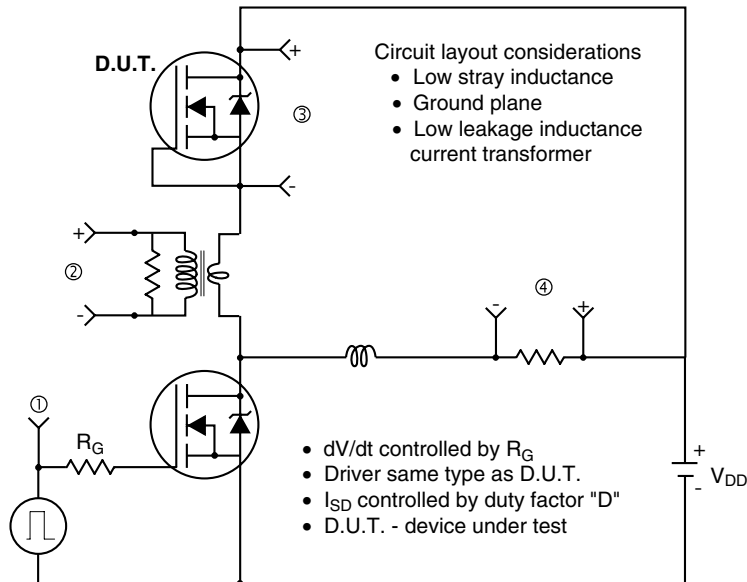
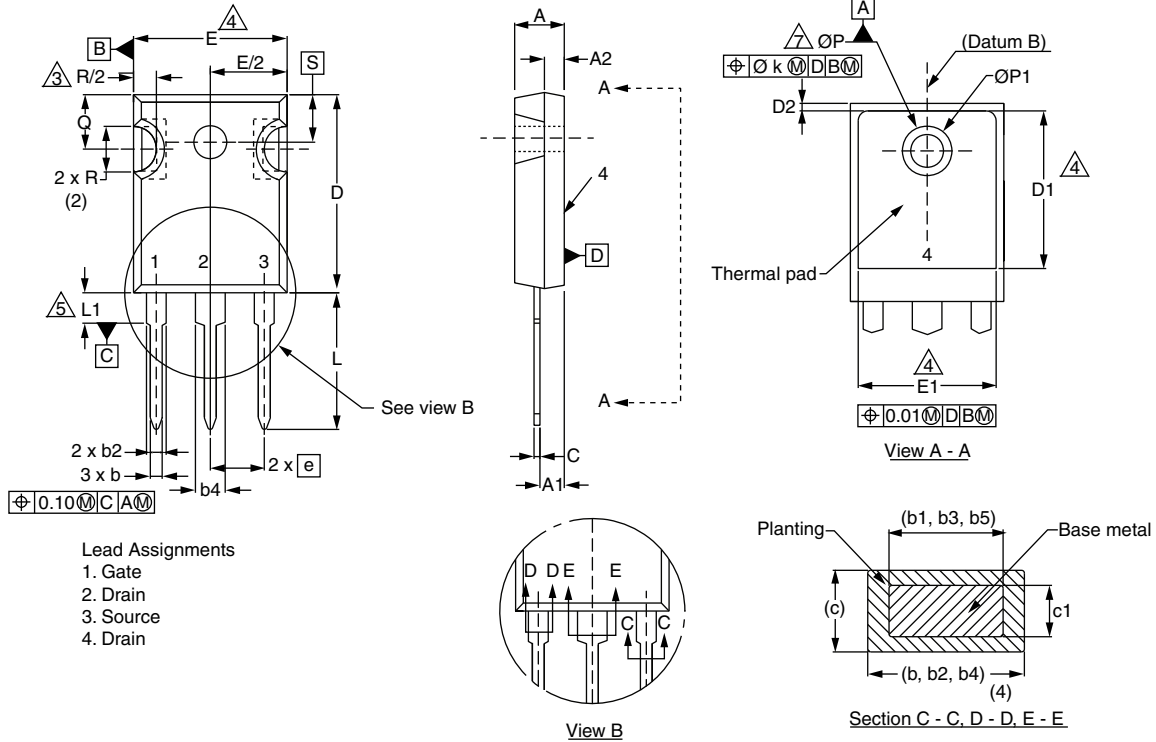


Fig. 14 - For N-Channel

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TO-247AC (High Voltage)



| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|-------|--------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 4.58 | 5.31 | 0.180 | 0.209 |
| A1 | 2.21 | 2.59 | 0.087 | 0.102 |
| A2 | 1.17 | 2.49 | 0.046 | 0.098 |
| b | 0.99 | 1.40 | 0.039 | 0.055 |
| b1 | 0.99 | 1.35 | 0.039 | 0.053 |
| b2 | 1.53 | 2.39 | 0.060 | 0.094 |
| b3 | 1.65 | 2.37 | 0.065 | 0.093 |
| b4 | 2.42 | 3.43 | 0.095 | 0.135 |
| b5 | 2.59 | 3.38 | 0.102 | 0.133 |
| c | 0.38 | 0.86 | 0.015 | 0.034 |
| c1 | 0.38 | 0.76 | 0.015 | 0.030 |
| D | 19.71 | 20.82 | 0.776 | 0.820 |
| D1 | 13.08 | - | 0.515 | - |

| DIM. | MILLIMETERS | | INCHES | |
|------|-------------|-------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| D2 | 0.51 | 1.30 | 0.020 | 0.051 |
| E | 15.29 | 15.87 | 0.602 | 0.625 |
| E1 | 13.72 | - | 0.540 | - |
| e | 5.46 BSC | | 0.215 BSC | |
| Ø k | 0.254 | | 0.010 | |
| L | 14.20 | 16.25 | 0.559 | 0.640 |
| L1 | 3.71 | 4.29 | 0.146 | 0.169 |
| N | 7.62 BSC | | 0.300 BSC | |
| Ø P | 3.51 | 3.66 | 0.138 | 0.144 |
| Ø P1 | - | 7.39 | - | 0.291 |
| Q | 5.31 | 5.69 | 0.209 | 0.224 |
| R | 4.52 | 5.49 | 0.178 | 0.216 |
| S | 5.51 BSC | | 0.217 BSC | |

ECN: X13-0103-Rev. D, 01-Jul-13
DWG: 5971

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6. Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.
8. Xian and Mingxin actually photo.





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